

120V N-Channel Enhancement Mode MOSFET

Description

The AP30N12D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 120V$ $I_D = 30A$

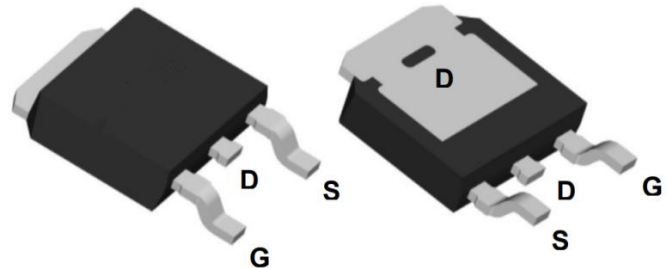
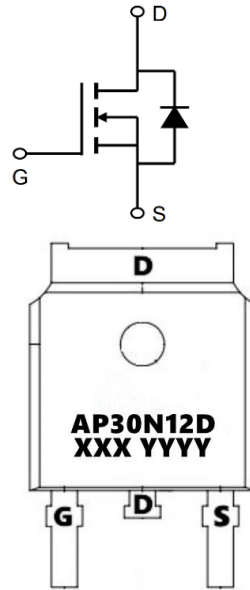
$R_{DS(ON)} < 75m\Omega @ V_{GS}=10V$ (Type: **50mΩ**)

Application

Automotive lighting

Load switch

Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP30N12D	TO-252-3L	AP30N12D XXX YYYY	2500

Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	120	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C=25^\circ C$	Drain Current, $V_{GS} @ 10V$	30	A
$I_D @ T_C=100^\circ C$	Drain Current, $V_{GS} @ 10V$	23	A
IDM	Pulsed Drain Current ¹	90	A
$P_D @ T_C=25^\circ C$	Total Power Dissipation	30	W
$P_D @ T_A=25^\circ C$	Total Power Dissipation ³	5	W
TSTG	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Maximum Thermal Resistance, Junctionambient	62.5	°C/W
$R_{\theta JC}$	Maximum Thermal Resistance, Junction-case	3.6	°C/W



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Electrical Characteristics@T_j=25°C(unless otherwise specified)

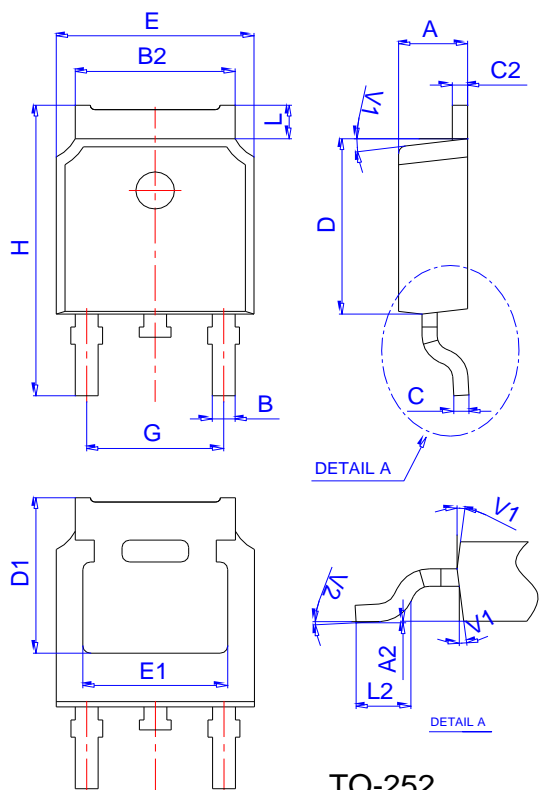
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	VGS=0V, ID=250μA	120	135	-	V
IDSS	Zero Gate Voltage Drain Current	VDS=100V, VGS=0V,	-	-	1.0	μA
IGSS	Gate to Body Leakage Current	VDS=0V, VGS=±20V	-	-	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250μA	1.2	2.0	2.5	V
RDS(on)	Static Drain-Source on-Resistance note3	VGS=10V, ID=5A	-	50	75	mΩ
		VGS=4.5V, ID=3A	-	65	90	mΩ
g fs	Forward Transconductance	V DS =5V , I D =5A		28		S
RG	Gate Resistance	VDS = 0V, VGS =0V,f =1MHz		3		Ω
Ciss	Input Capacitance	VDS=15V, VGS=0V, f=1.0MHz	-	2200	-	pF
Coss	Output Capacitance		-	110	-	pF
Crss	Reverse Transfer Capacitance		-	80	-	pF
Qg	Total Gate Charge	VDS=50V, ID=10A, VGS=10V	-	24	-	nC
Qgs	Gate-Source Charge		-	5.6	-	nC
Qgd	Gate-Drain("Miller") Charge		-	3.4	-	nC
td(on)	Turn-on Delay Time	VDS=30V, ID=10A, RG=1.8Ω, VGS=10V	-	7.6	-	ns
tr	Turn-on Rise Time		-	52	-	ns
td(off)	Turn-off Delay Time		-	32	-	ns
tf	Turn-off Fall Time		-	18	-	ns
IS	Continuous Source Current1,5	VG=VD=0V , Force Current	-	-	30	A
ISM	Pulsed Source Current2,5		-	-	90	A
VSD	Diode Forward Voltage2	VGS=0V, IS=10A	-	-	1.2	V

Note :

- 1、 The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3、 The power dissipation is limited by 150°C junction temperature
- 4、 The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

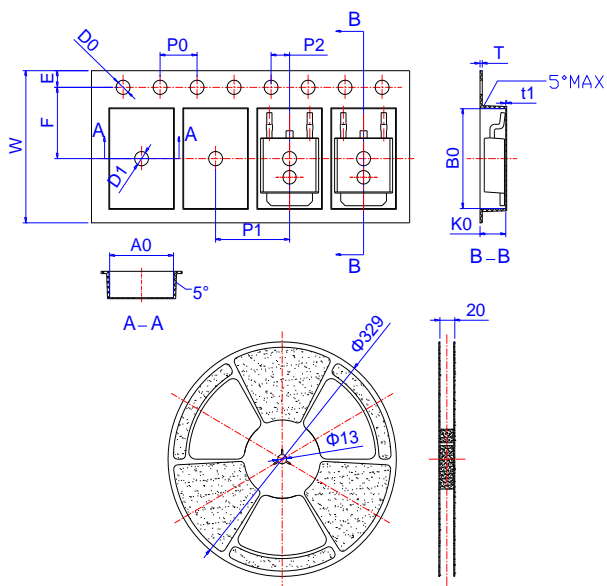
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Package Mechanical Data:TO-252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583